

December 1997

Features

- QML Qualified Per MIL-PRF-38535 Requirements
- 1.25Micron Radiation Hardened SOS CMOS
- Radiation Environment
 - Latch-up Free Under any Conditions
 - Total Dose 3×10^5 RAD(Si)
 - SEU Immunity $<1 \times 10^{-10}$ Errors/Bit/Day
 - SEU LET Threshold >100 MeV/(mg/cm²)
- Input Logic Levels $V_{IL} = 0.8V, V_{IH} = (V_{CC}/2)$
- Output Current $\pm 12mA$
- Quiescent Supply Current $20\mu A$
- Propagation Delay 20ns

Applications

- Memory Decoding
- Data Routing
- Code Conversion

Description

The Radiation Hardened ACTS138MS is an Inverting 3-to-8 Line Decoder/Demultiplexer with three TTL level binary select inputs (A_0, A_1 and A_2). If the device is enabled, these inputs determine which one of the eight normally high outputs will go low.

Two active low and one active high enable inputs (\bar{E}_1, \bar{E}_2 and E_3) are provided to make cascaded decoder designs easier to implement.

The ACTS138MS is fabricated on a CMOS Silicon on Sapphire (SOS) process, which provides an immunity to Single Event Latch-up and the capability of highly reliable performance in any radiation environment. These devices offer significant power reduction and faster performance when compared to ALSTTL types.

Specifications for Rad Hard QML devices are controlled by the Defense Supply Center in Columbus (DSCC). The SMD numbers listed below must be used when ordering.

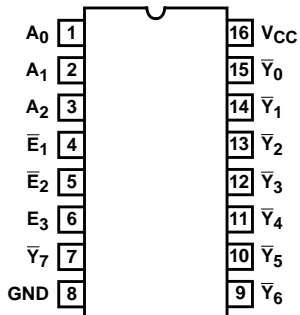
Detailed Electrical Specifications for the ACTS138 are contained in SMD 5962-98535. A "hot-link" is provided on our homepage with instructions for downloading. <http://www.intersil.com/data/sm/index.htm>

Ordering Information

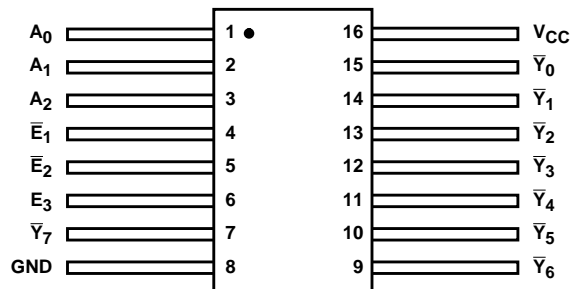
SMD PART NUMBER	INTERSIL PART NUMBER	TEMP. RANGE (°C)	PACKAGE	CASE OUTLINE
5962F9853501VEC	ACTS138DMSR-02	-55 to 125	16 Ld SBDIP	CDIP2-T16
N/A	ACTS138D/Sample-02	25	16 Ld SBDIP	CDIP2-T16
5962F9853501VXC	ACTS138KMSR-02	-55 to 125	16 Ld Flatpack	CDFP4-F16
N/A	ACTS138K/Sample-02	25	16 Ld Flatpack	CDFP4-F16
N/A	ACTS138HMSR-02	25	Die	N/A

Pinouts

ACTS138 (SBDIP)
TOP VIEW



ACTS138 (FLATPACK)
TOP VIEW



ACTS138MS

Die Characteristics

DIE DIMENSIONS:

Size: 2390 μ m x 2390 μ m (94 mils x 94 mils)
Thickness: 525 μ m \pm 25 μ m (20.6 mils \pm 1 mil)
Bond Pad: 110 μ m x 110 μ m (4.3 x 4.3 mils)

METALLIZATION: Al

Metal 1 Thickness: 0.7 μ m \pm 0.1 μ m
Metal 2 Thickness: 1.0 μ m \pm 0.1 μ m

SUBSTRATE POTENTIAL:

Unbiased Insulator

PASSIVATION

Type: Phosphorous Silicon Glass (PSG)
Thickness: 1.30 μ m \pm 0.15 μ m

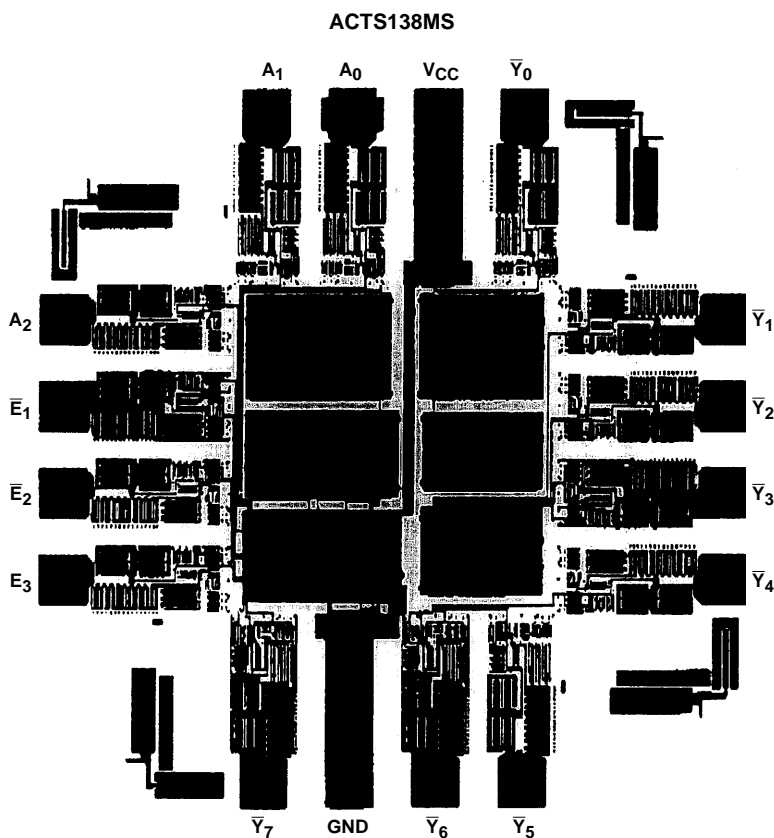
SPECIAL INSTRUCTIONS:

Bond V_{CC} First

ADDITIONAL INFORMATION:

Worst Case Density: <2.0 x 10⁵ A/cm²
Transistor Count: 256

Metallization Mask Layout



All Intersil semiconductor products are manufactured, assembled and tested under **ISO9000** quality systems certification.

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